

JIEJIE MICROELECTRONICS CO., LTD.



Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	1	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=110$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	5	mA
I_H	$I_T=0.05A$	-	-	4	mA
dV/dt	$V_D=800V T_j=110 R_{GK}=1k$	200	-	-	$V/\mu s$
	$V_D=800V T_j=110 R_{GK}=220$	1000	-	-	

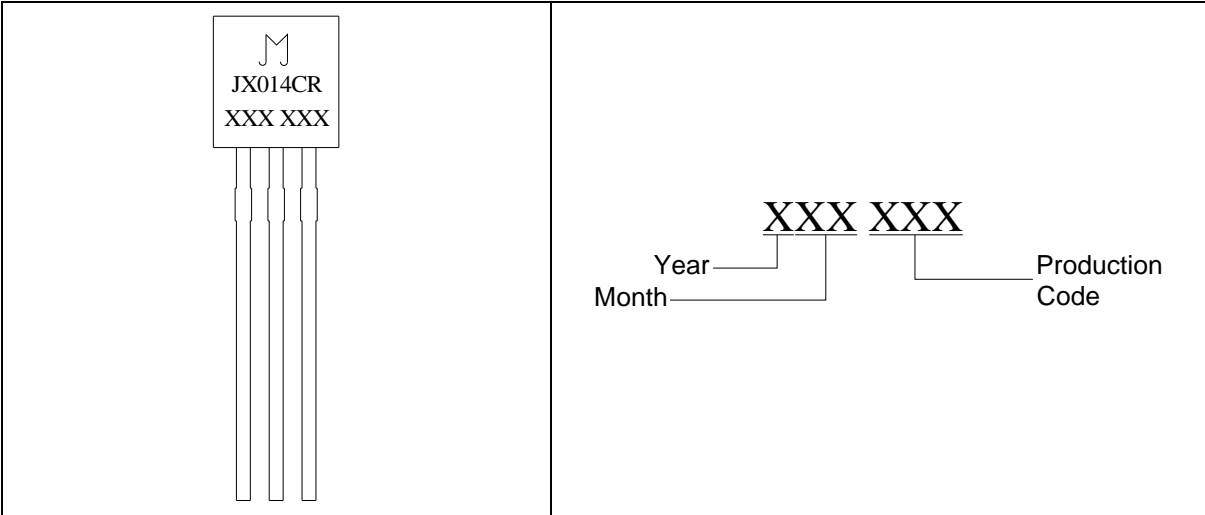
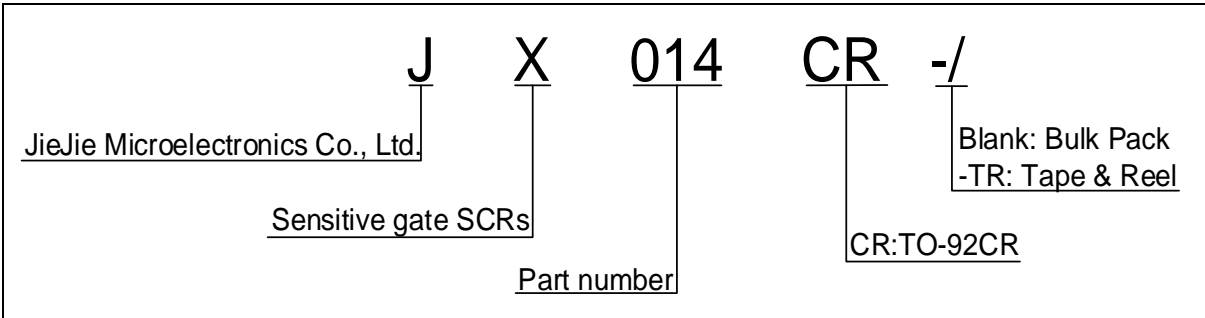
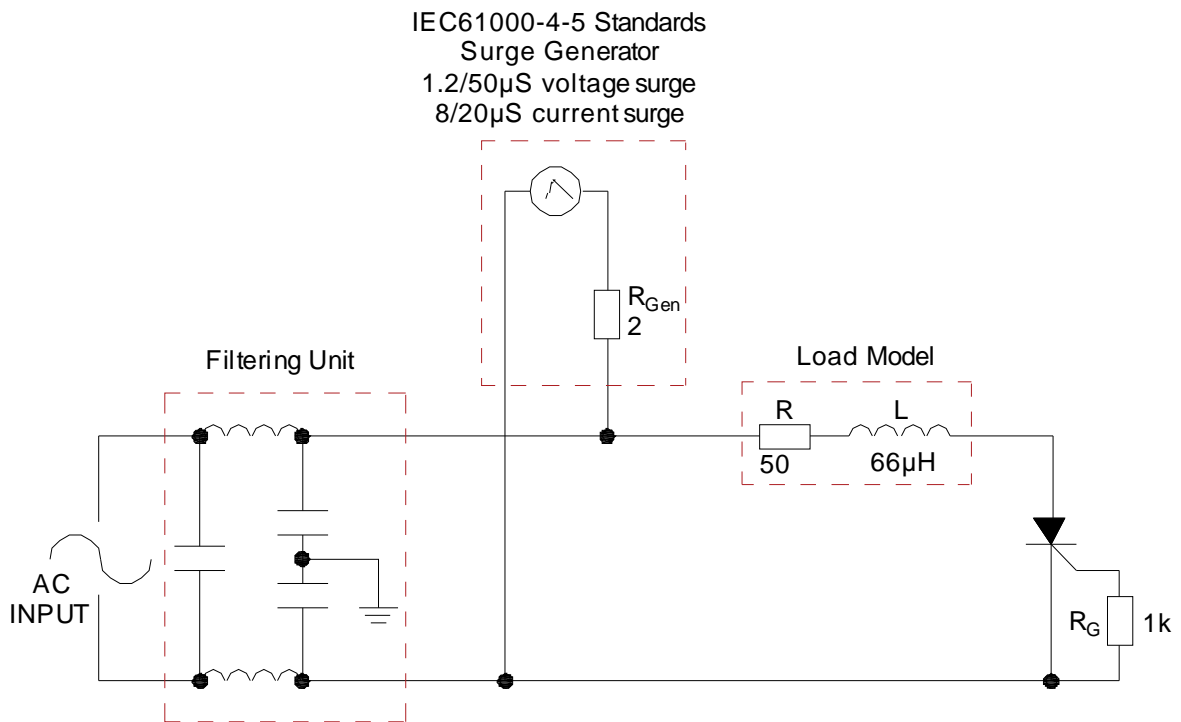


FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics



